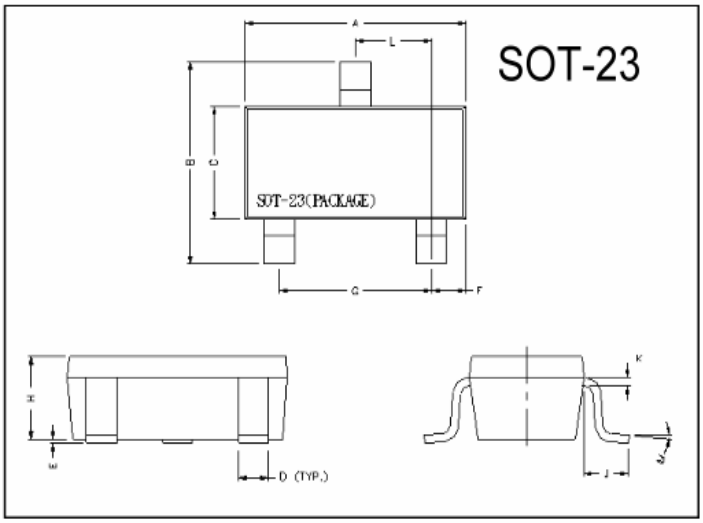
GMBT5089

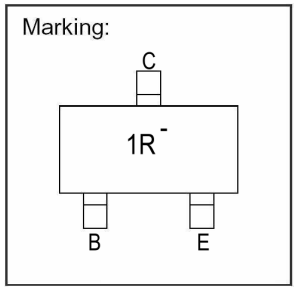
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT5089 is designed for low noise, high gain, general purpose amplifier applications.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90 REF.	
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings

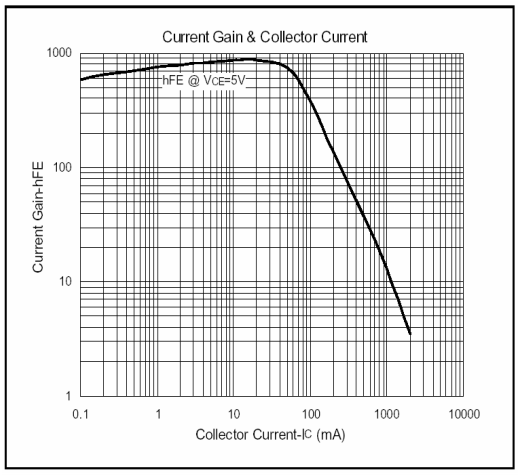
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	30	V
Collector to Emitter Voltage	VCEO	25	V
Emitter to Base Voltage	VEBO	4.5	V
Collector Current	IC	50	mA
Total Power Dissipation	PD	225	mW

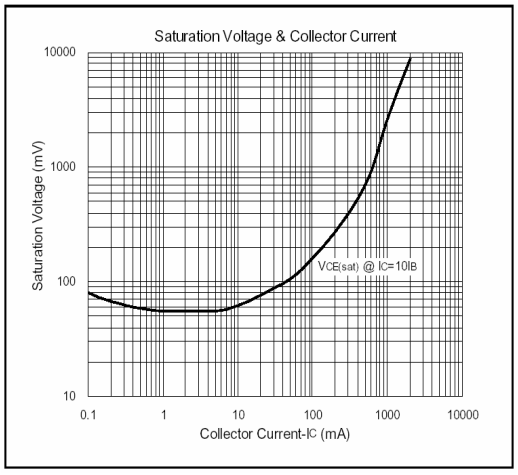
Characteristics at Ta = 25℃

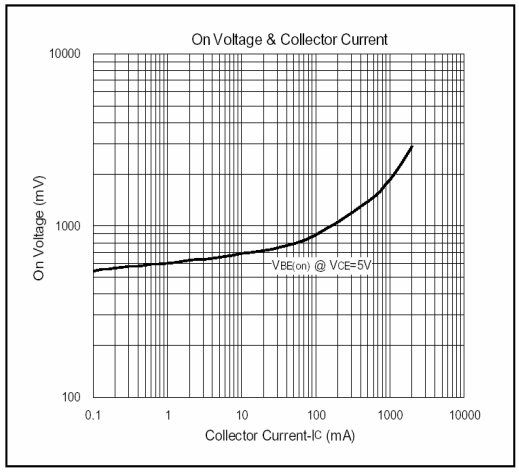
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	30	-	-	V	IC=100uA
BVCEO	25	-	-	V	IC=1mA
BVEBO	4.5	-	-	V	IE=10uA
ICBO	-	-	50	nA	VCB=15V
IEBO	-	-	100	nA	VEB=4.5V
*VCE(sat)	-	-	500	mV	IC=10mA, IB=1mA
*VBE(sat)	-	-	800	mV	IC=10mA, IB=1mA
hFE1	400	-	1200		VCE=5V, IC=0.1mA
hFE2	450	-			VCE=5V, IC=1mA
hFE3	400	-	-		VCE=5V, IC=10mA
fT	50		-	MHz	VCE=5V, IC=0.5mA, f=20MHz
Cob	-	-	4	pF	VCB=5V, f=1MHz

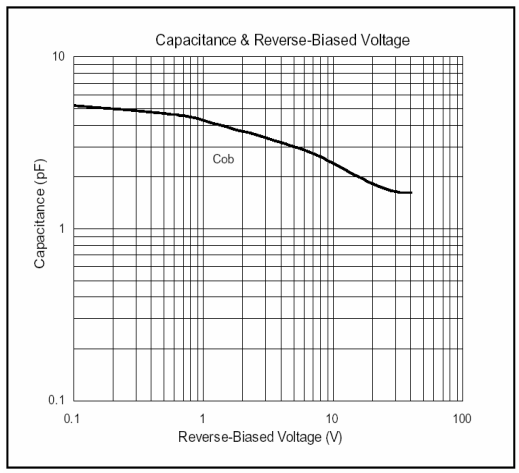
*Pulse Test:Pulse Width <=380us, Duty Cycle <=2%

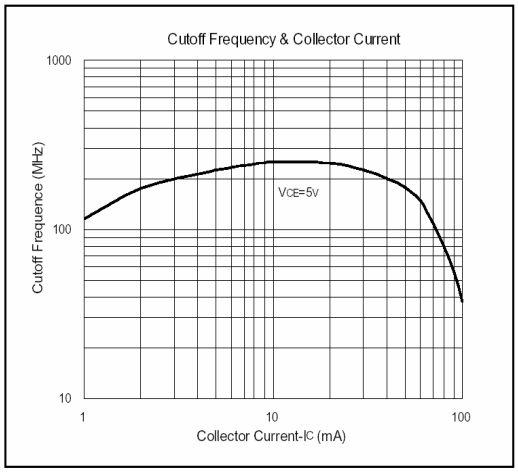
Characteristics Curve

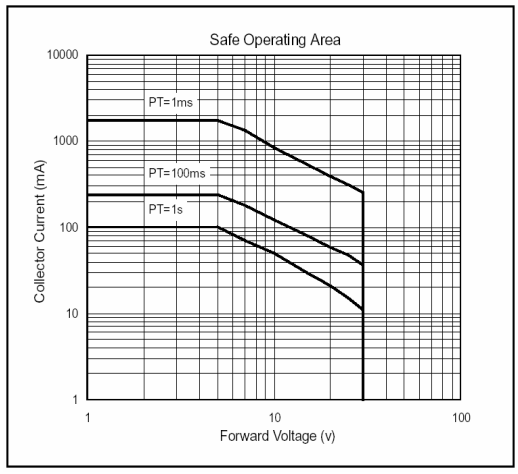












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